

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030242US1	Application No. 10/715,400	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Dureseti CHIDAMBARRAO				
		Filing Date 11/19/2003		Group 2813		

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EXAMINER	<i>JAM</i>	DATE CONSIDERED	<i>9/20/06</i>
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